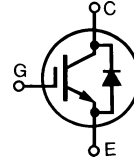


# High Voltage IGBT with Diode

**IXSK 35N120BD1**  
**IXSX 35N120BD1**

**$V_{CES} = 1200\text{ V}$**   
 **$I_{C25} = 70\text{ A}$**   
 **$V_{CE(SAT)} = 3.6\text{ V}$**

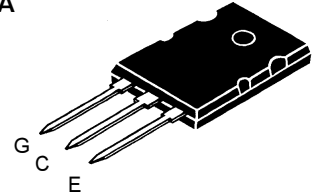
Short Circuit SOA Capability



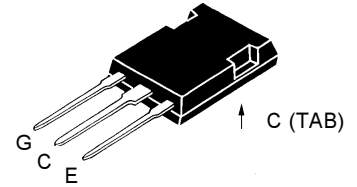
Preliminary data sheet

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1200	V
$V_{CGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1\text{ M}\Omega$	1200	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	70	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	35	A
$I_{CM}$	$T_C = 25^\circ\text{C}, 1\text{ ms}$	140	A
<b>SSOA (RBSOA)</b>	$V_{GE} = 15\text{ V}, T_J = 125^\circ\text{C}, R_G = 5\ \Omega$ Clamped inductive load	$I_{CM} = 90$ @ $0.8 V_{CES}$	A
<b><math>t_{SC}</math> (SCSOA)</b>	$V_{GE} = 15\text{ V}, V_{CE} = 720\text{ V}, T_J = 125^\circ\text{C}$ $R_G = 5\ \Omega$ , non repetitive	10	$\mu\text{s}$
$P_C$	$T_C = 25^\circ\text{C}$	IGBT	300 W
		Diode	190 W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
<b>Weight</b>	TO-264	10	g
	PLUS247	6	g

**TO-264 AA (IXSK)**



**PLUS TO-247™ (IXSX)**



G = Gate,  
E = Emitter,

C = Collector,  
TAB = Collector

## Features

- Hole-less TO-247 package for clip mounting
- High frequency IGBT and anti-parallel FRED in one package
- Low  $V_{CE(sat)}$ 
  - for minimum on-state conduction losses
- MOS Gate turn-on
  - drive simplicity
- Fast Recovery Epitaxial Diode (FRED)
  - soft recovery with low  $I_{RM}$

## Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

## Advantages

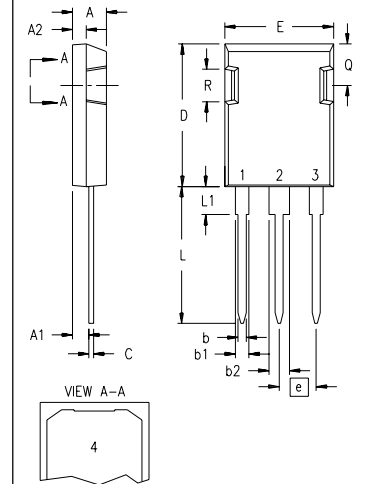
- Space savings (two devices in one package)
- Reduces assembly time and cost
- High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$BV_{CES}$	$I_C = 3\text{ mA}, V_{GE} = 0\text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 250\ \mu\text{A}, V_{CE} = V_{GE}$	3		V
$I_{CES}$ ①	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0\text{ V}$ $T_J = 125^\circ\text{C}$			1 mA 3 mA
$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15\text{ V}$			3.6 V

① Device must be heatsunk for high temperature measurements to avoid thermal runaway.  
IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$g_{fs}$	$I_C = I_{C90}$ ; $V_{CE} = 10\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $\leq 2\%$	16	23	S	
$C_{ies}$	$V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$ , $f = 1\text{ MHz}$		3600	pF	
$C_{oes}$			315	pF	
$C_{res}$			75	pF	
$Q_g$	$I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ , $V_{CE} = 0.5 V_{CES}$		120	nC	
$Q_{ge}$			33	nC	
$Q_{gc}$			49	nC	
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ , $V_{CE} = 0.8 V_{CES}$ , $R_G = 5.0\ \Omega$ Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		36	ns	
$t_{ri}$			27	ns	
$t_{d(off)}$			160	300	ns
$t_{fi}$			180	300	ns
$E_{off}$			5	9	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ , $V_{CE} = 0.8 V_{CES}$ , $R_G = 5.0\ \Omega$ Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		38	ns	
$t_{ri}$			29	ns	
$E_{on}$			6	mJ	
$t_{d(off)}$			240	ns	
$t_{fi}$			340	ns	
$E_{off}$		9	mJ		
$R_{thJC}$			0.42	KW	
$R_{thCK}$		0.15		KW	

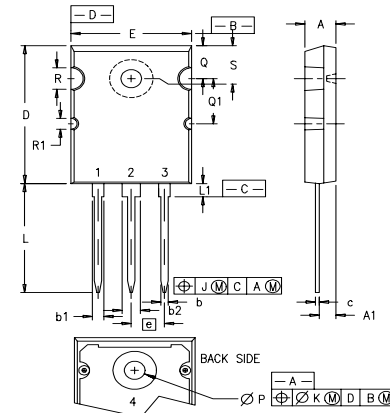
### TO-247 HOLE-LESS Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83

- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - DRAIN (COLLECTOR)

### TO-264 AA Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

- 1 - GATE
- 2, 4 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_F$	$I_F = 130\text{ A}$ , $V_{GE} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$ , $T_J = 125^\circ\text{C}$			2.75 V 1.85 V
$I_{RM}$	$I_F = 130\text{ A}$ , $V_{GE} = 0\text{ V}$ , $-di_F/dt = 100\text{ A}/\mu\text{s}$ , $T_J = 100^\circ\text{C}$ $V_R = 100\text{ V}$		7	14.3 A
$t_{rr}$			40	ns
$R_{thJC}$				0.65 KW

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715  
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025